line 5, before "formed" insert --is--;

line 7, after "substrate" delete "; and a"
and insert therefor --. A--;

line 7, before "filled" insert --is--;

Page 6, line 3, delete "11" and insert therefor
--111--;

Page 7, line 1, delete "owing" and insert therefor
--due--;

IN THE CLAIMS:

1. (Once Amended) A dynamic random access memory having a
trench capacitor, said memory comprising:

a semiconductor substrate of one conduction type;

a trench formed in said semiconductor substrate;

a first conductive layer formed on <u>a deep portion</u> [the]
<u>of an</u> inner surface of said trench <u>and not being formed in</u>
[except for] a region [adjacent] <u>close</u> to [the opening portion]
<u>an entrance</u> of said trench;

a dielectric layer <u>being</u> formed on said first
conductive layer [exposed] in said trench and <u>being formed on</u>
<u>said inner</u> [the] surface of <u>said trench in said region close to</u>
<u>said entrance of said trench</u> [said semiconductor substrate];

a second conductive layer [filled] <u>filling</u> in said
trench through said dielectric layer;

said first conductive layer, said dielectric layer, and
said second conductive layer constituting a storage capacitor;
and

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